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Symbol	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	224	
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	141	Α
I _{DM}	Pulsed Drain Current	896	
P _D @T _C = 25°C	Power Dissipation	208	W
V _{DS}	Drain-Source Voltage	100	V
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS}	Single Pulse Avalanche Energy @ L=0.5mH	795	mJ
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

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Symbol	Characterizes	Тур.	Max.	Units
	Junction-to-case			
	Junction-to-ambient (t $\leq 10s$)			

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Symbol	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source breakdown voltage	100			V	$V_{GS} = 0V, I_D$
R _{DS(on)}	Static Drain-to-Source on-resistance		1.8	3	m	V _{GS} =10V,I _D = 50A
V _{GS(th)}	Gate threshold voltage	2		4	V	$V_{DS} = V_{GS}, I_{D}$
I _{DSS}	Drain-to-Source leakage current			1		$V_{DS} = 100V, V_{GS} = 0V$
I _{GSS}	Gate-to-Source forward leakage			100	nA	V _{GS} =20V
				-100		V _{GS} = -20V
C _{iss}	Input capacitance		6209			V _{GS} = 0V
Coss	Output capacitance		2570		pF	V _{DS} = 50V
C _{rss}	Reverse transfer capacitance		67			100kHz

Q_g Total gate charge





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Calculated continuous current based on maximum allowable junction temperature.

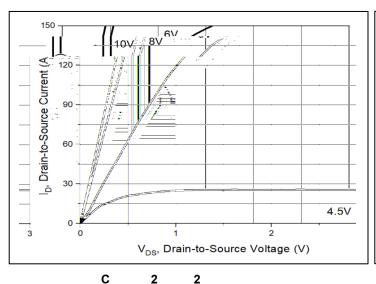
Repetitive rating; pulse width limited by max. junction temperature.

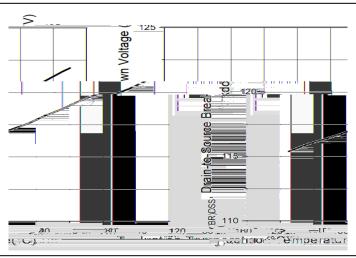
The power dissipation P_D is based on max. junction temperature, using junction-to-case thermal resistance.

The value of $\,$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A



Typical Electrical and Thermal Characteristics

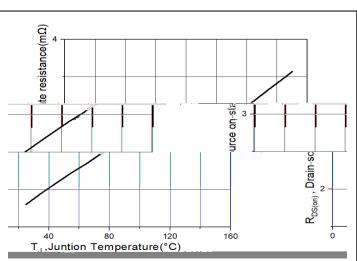


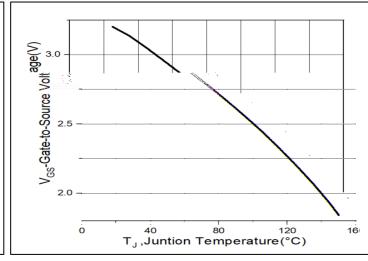


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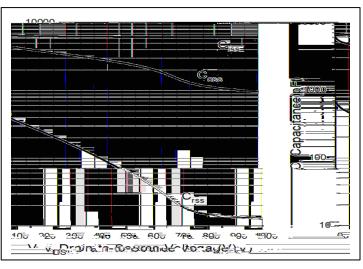
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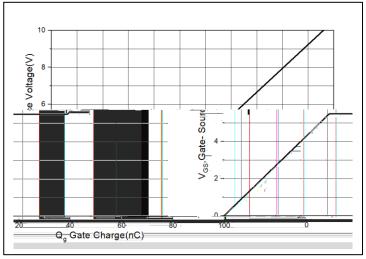
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Figure5. Capacitance

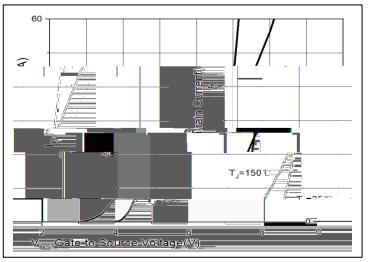
Figure6. Gate Charge

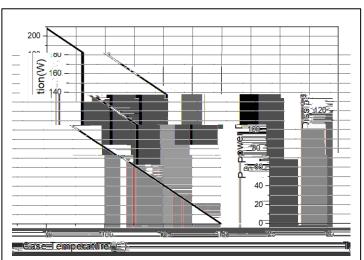
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Typical Electrical and Thermal Characteristics

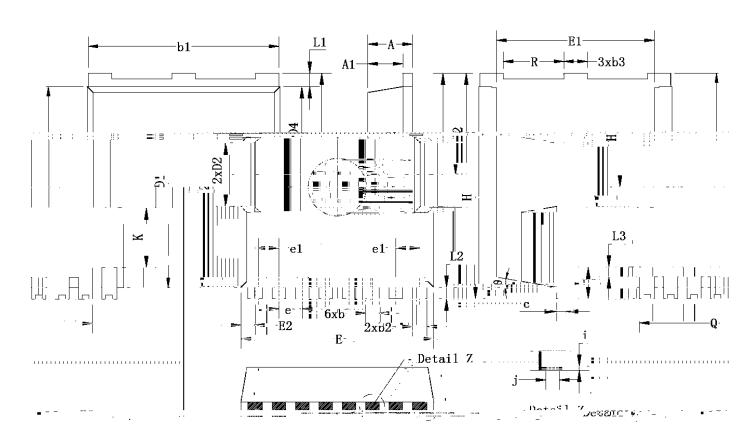




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Symbol	Min	Тур	Max	Symbol	Min	Тур	Max
, III Å	2 25	2 30	?35	F2	U 62	-0.70	0 75
11.80	A1	1.75	—1 .80	==1.8≶	H	- 11.6	0 = 11.70
C		0.65	0.70	0.75	Hl		6.95 BS
C.		9.75	9.80	9.85	H2:		5.90 BS
:F	b2	0.70	0.75	0.80			0.10 R F
TP.	h3	1 15	1.20	.1.25	· was de		n 35. P F
	3.10 RHG						K
J. 64		1.78		1,0,3%		10,4%	
9.70			11.00 - 11	.10 11.29		11.1.1	0.65
970: L3%		<u>- 1</u>		30a) 1			ari Ariga
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